

# Partnership Between Universities & Industrial Labs

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# Outline

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- Why Darpa is important
- Role of the University
- Role of the Industrial Lab
- Rules of Engagement

# Darpa as DoD VC

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Chart 3

- Central R&D for the Department of Defense
- Fundamental Discoveries to their Military use
- Military Roles and Missions

# DoD VC

- Central R&D for the Department of Defense
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- Military Roles and Missions
- Everything in the context of a PM

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- High-Risk High-Payoff

# DoD VC

- Central R&D for the Department of Defense
- Fundamental Discoveries to their Military use
- Military Roles and Missions
- Everything in the context of a PM
- High-Risk High-Payoff
- Adequate funding...

# ...And Go/No-Go Milestones

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Chart 7

Universities have them – they are called Exams

# Recent Programs with University Collaborators

Chart 8

More than 50% of Teledyne programs include Universities

ABCS

TFAST

FLARE

gBECi

MIATA

CSAC

SMART

Sb-SLS

TIFT

# Recent Programs with University Collaborators

More than 50% of Teledyne programs include Universities

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And a great majority of those  
are sponsored by Darpa

# Outline

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- **Role of the University**
- Role of the Industrial Lab
- Rules of Engagement

# Role of the University

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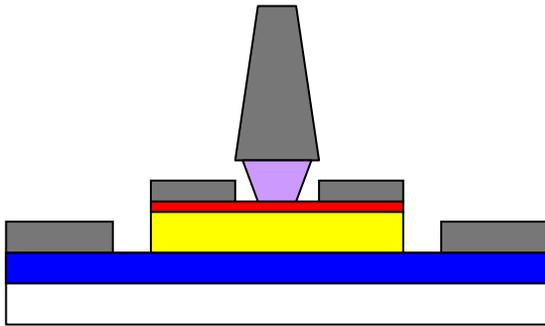
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Chart 11

- They are good at the fundamentals

# Collaboration on TFAST

University set the stage:  
InP HBT Scaling Roadmaps



Parameter	scaling law	Gen. 2 (500 nm)	Gen. 3 (250 nm)	Gen. 4 (125 nm)	Gen 5 (62.5nm)
MS-DFF speed	$\gamma^1$	150 GHz	235 GHz	330 GHz	440 GHz
Amplifier center frequency	$\gamma^1$	245 GHz	400 GHz	650 GHz	750 GHz
Emitter Width	$1/\gamma^2$	500 nm	250 nm	125 nm	62.5 nm
Resistivity	$1/\gamma^2$	16 $\Omega\text{-}\mu\text{m}^2$	9 $\Omega\text{-}\mu\text{m}^2$	4 $\Omega\text{-}\mu\text{m}^2$	2 $\Omega\text{-}\mu\text{m}^2$
Base Thickness	$1/\gamma^{1/2}$	300 Å	250 Å	212 Å	180 Å
Contact width	$\sim 1/\gamma^2$	300 nm	175 nm	120 nm	70 nm
Doping	$\gamma^0$	7 $10^{19}/\text{cm}^2$	7 $10^{19}/\text{cm}^2$	7 $10^{19}/\text{cm}^2$	7 $10^{19}/\text{cm}^2$
Sheet resistance	$\gamma^{1/2}$	500 $\Omega$	600 $\Omega$	707 $\Omega$	830 $\Omega$
Contact $\rho$	$1/\gamma^{1/2}$	20 $\Omega\text{-}\mu\text{m}^2$	10 $\Omega\text{-}\mu\text{m}^2$	5 $\Omega\text{-}\mu\text{m}^2$	5 $\Omega\text{-}\mu\text{m}^2$
Collector Width	$1/\gamma^2$	1.2 $\mu\text{m}$	0.60 $\mu\text{m}$	0.37 $\mu\text{m}$	0.20 $\mu\text{m}$
Thickness	$1/\gamma$	1500 Å	1060 Å	750 Å	530 Å
Current Density	$\gamma^2$	4.5 $\text{mA}/\mu\text{m}^2$	9 $\text{mA}/\mu\text{m}^2$	18 $\text{mA}/\mu\text{m}^2$	36 $\text{mA}/\mu\text{m}^2$
$A_{\text{collector}}/A_{\text{emitter}}$	$\gamma^0$	2.4	2.4	2.9	2.8
$f_T$	$\gamma^1$	370 GHz	530 GHz	730 GHz	1.0 THz
$f_{\text{max}}$	$\gamma^1$	490 GHz	801 GHz	1.30 THz	1.5 THz
$I_E / L_E$	$\gamma^0$	2.3 $\text{mA}/\mu\text{m}$	2.3 $\text{mA}/\mu\text{m}$	2.3 $\text{mA}/\mu\text{m}$	2.3 $\text{mA}/\mu\text{m}$
$\tau_f$	$1/\gamma$	340 fs	240 fs	180 fs	130 fs
$C_{cb} / I_c$	$1/\gamma$	400 fs/V	280 fs/V	250 fs/V	190 fs/V
$C_{cb} \Delta V_{\text{logic}} / I_c$	$1/\gamma$	120 fs	85 fs	74 fs	57 fs
$R_{bb} / (\Delta V_{\text{logic}} / I_c)$	$\gamma^0$	0.76	0.54	0.34	0.39
$C_{je} (\Delta V_{\text{logic}} / I_c)$	$1/\gamma^{3/2}$	380 fs	180 fs	94 fs	50 fs
$R_{ex} / (\Delta V_{\text{logic}} / I_c)$	$\gamma^0$	0.24	0.24	0.24	0.24

Chart 12

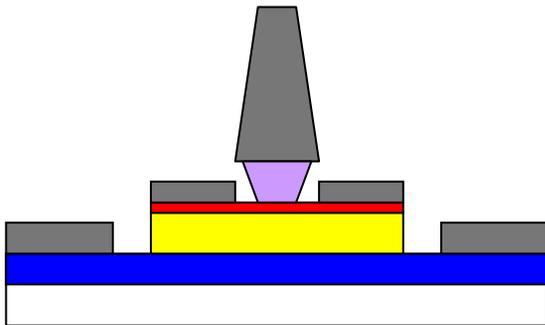


key figures of merit  
for logic speed

**Key scaling challenges** →  
emitter & base contact resistivity  
current density → device heating  
collector-base junction width scaling  
& Yield!

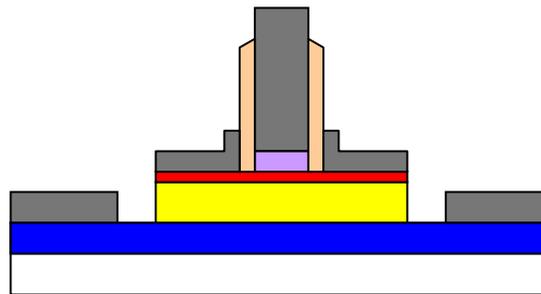
# Three+ Versions of Technology

## Scaled mesa-HBT



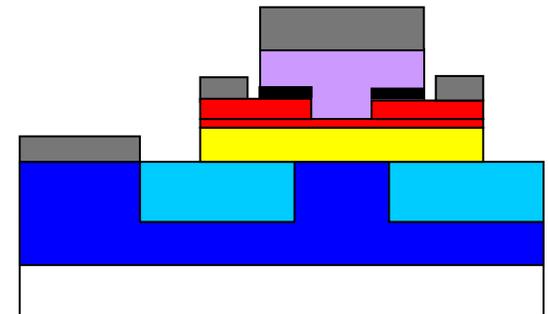
- High performance, low yield technology
- Difficult to scale to  $W_E < 0.3 \mu\text{m}$
- Processed for epitaxy and circuit validation
- Record device results obtained at UCSB

## S3 Technology



- Eliminate Lifftoff from Base-Emitter Junction Formation. High Yield.
- Process scalable to  $W_E < 0.25 \mu\text{m}$
- Integrated improved multi-level interconnect process
- Platform for fabrication of DDS and divider circuits

## Regrowth Technology



- Process modules that can be added to HBT technology
- Emitter regrowth for high yield, low  $\rho_{ex}$
- Pedestal implant for reduced  $C_{cb}$
- Subcollector implant for reduced  $C_{cb}$
- Process development at UCSB

# University Led with Devices and Process Modules

## Industry focused on ICs

### popular metrics :

$f_\tau$  or  $f_{\max}$  alone

$(f_\tau + f_{\max}) / 2$

$\sqrt{f_\tau f_{\max}}$

$(1/f_\tau + 1/f_{\max})^{-1}$

### *much better metrics :*

#### power amplifiers :

PAE, associated gain,  
mW/ $\mu\text{m}$

#### low noise amplifiers :

$F_{\min}$ , associated gain,

#### digital :

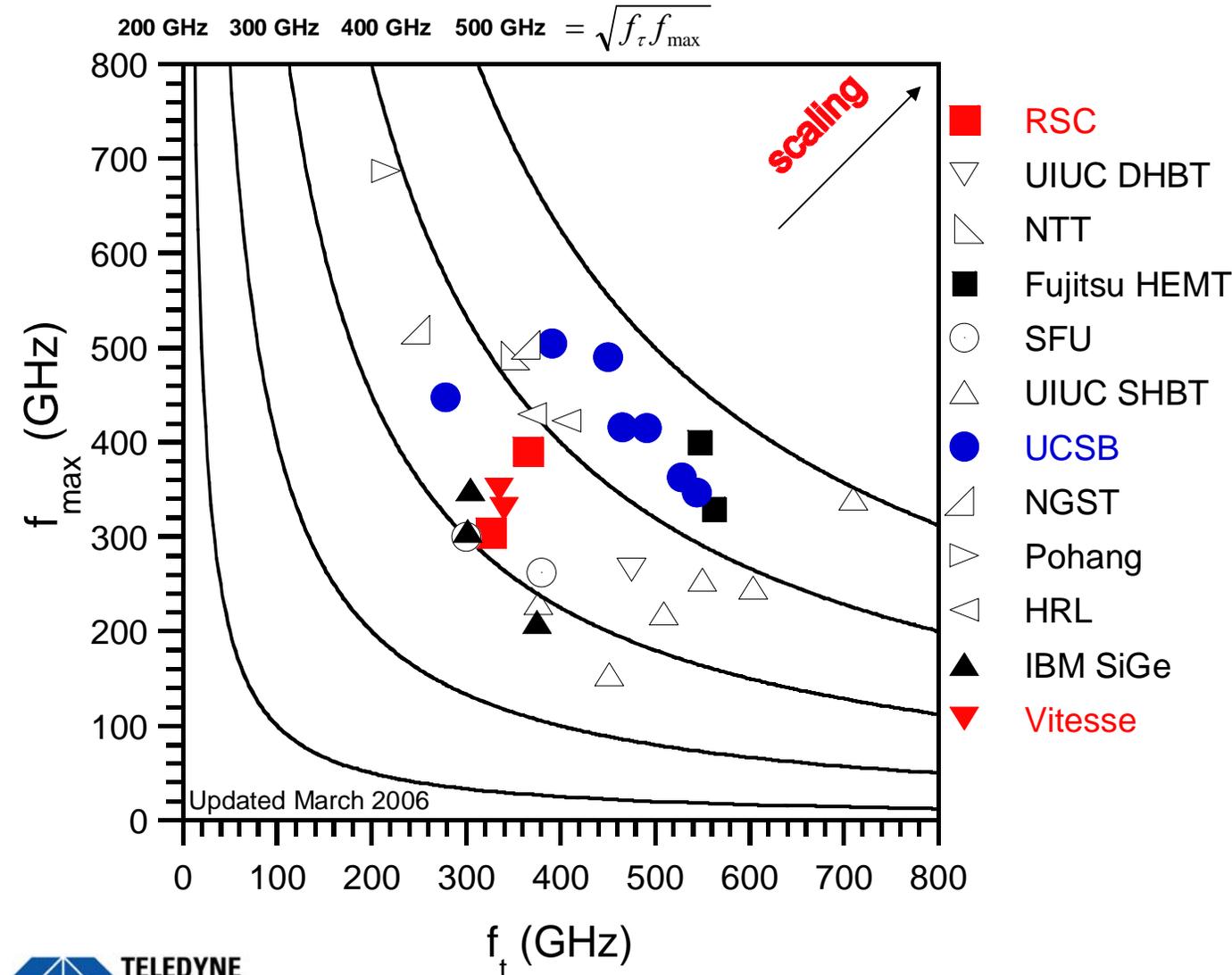
$f_{\text{clock}}$ , hence

$(C_{cb} \Delta V / I_c)$ ,

$(R_{ex} I_c / \Delta V)$ ,

$(R_{bb} I_c / \Delta V)$ ,

$(\tau_b + \tau_c)$

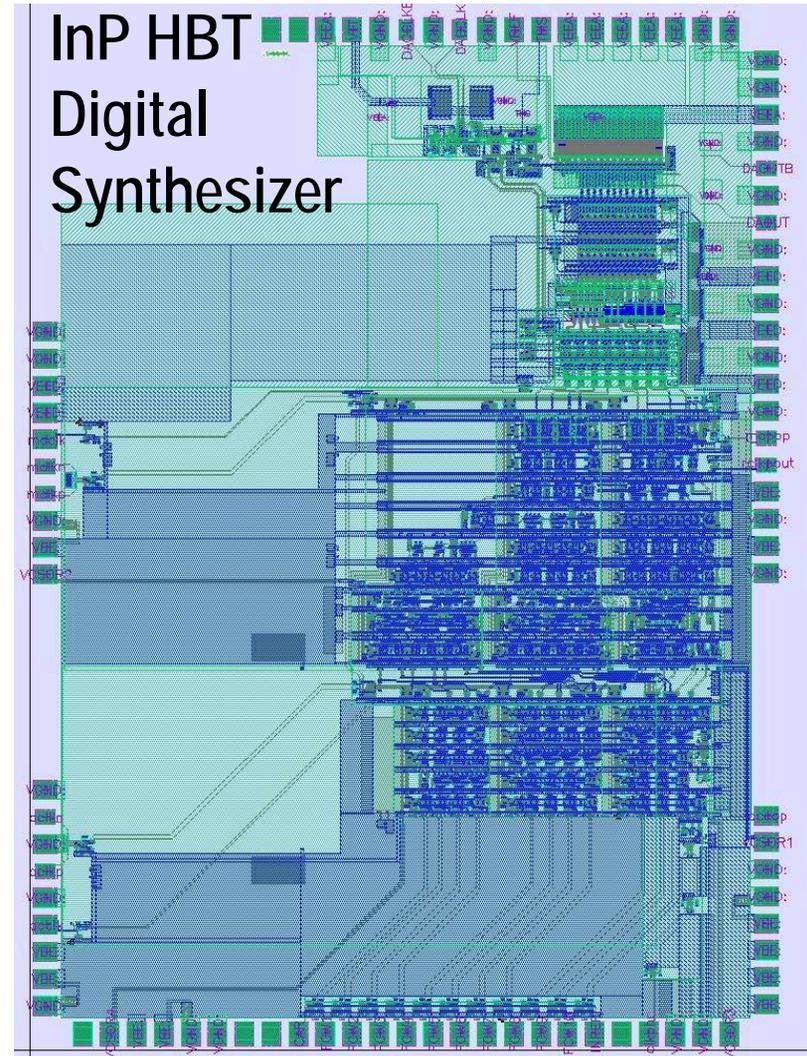


# Multiple circuit Iterations (takes a few years)

## The right role for industry

### New Technologies require

- Materials development
- Process development
- Process qualification
- Design kit development
- Yield improvement
- Complex circuit demonstrations



# Role of the University

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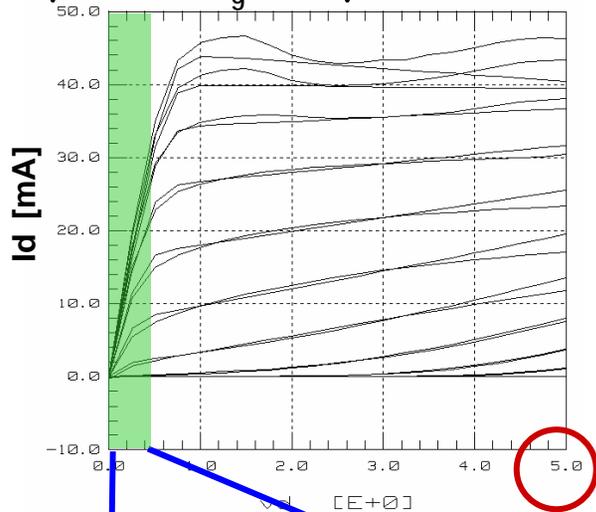
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Chart 16

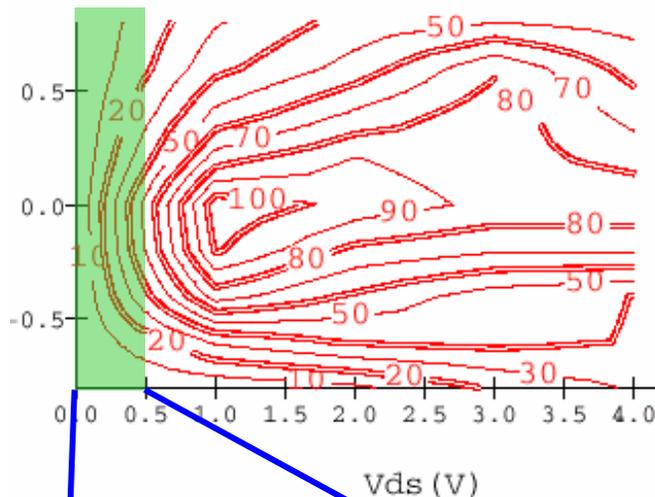
- They are good at the fundamentals
- They are more inclined to be objective

# ABCS HEMT technology enables MMW high-performance LNAs at 40x lower power than GaAs

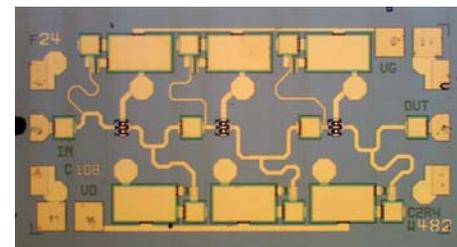
80 $\mu$ m wide,  $L_g=0.18 \mu$ m GaAs PHEMT



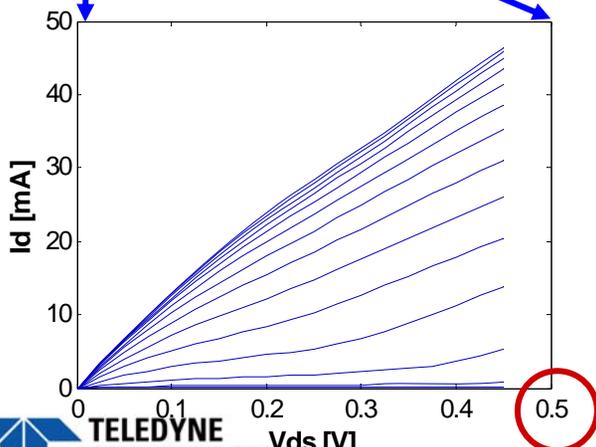
100GHz Ft at  $V_{ds} > 1V$



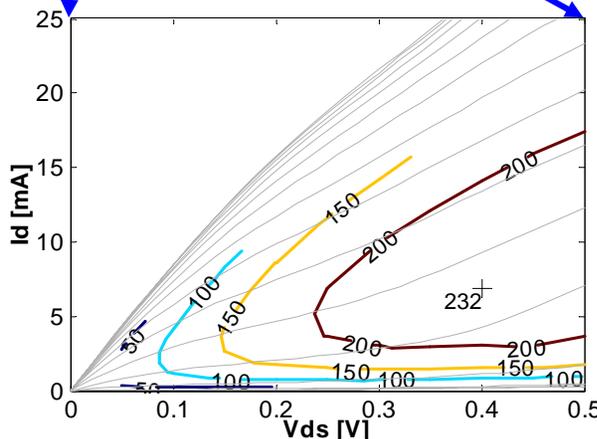
Ka-Band GaAs LNA  
4V, 40mA Fets  
Gain = 20-27dB, Power=160mW



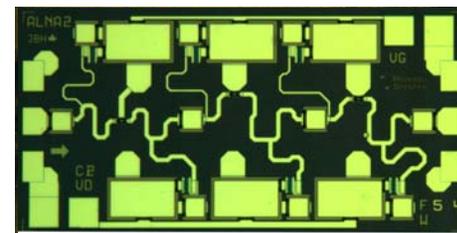
40 $\mu$ m wide,  $L_g=0.2 \mu$ m ABCS HEMT



100GHz Ft at  $V_{ds} = 0.1V$



Ka-Band ABCS LNA  
0.35V, 12mA Fets  
Gain = 28dB, NF < 2.2 dB  
Power=4.2mW



1/10<sup>th</sup> Voltage scale = same RF performance

# Role of the University

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Chart 18

- They are good at the fundamentals
- They are more inclined to be objective
- They need to publish, publish, publish

# Role of the University

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- They are good at the fundamentals
- They are more inclined to be objective
- They need to publish, publish, publish
- They can move fast
- They have students
- (Everything in the University is in the context of a student)

# Role of the University

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- Role of the University
- **Role of the Industrial Lab**
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# Role of the Industrial Lab

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Chart 22

- Industrial Lab (Teledyne Scientific's) Business Model

# Teledyne Business Model

## R&D Service & IP Creation

R&D Customers  
(Government & Private Sector)

Industrial Lab

- Contract R&D
- Tech transition
- IP Generation

University &  
other  
Partners

- Electronics
- Materials / Optics
- Information Science

## IP Value Realization

Licensing & Spin-out

Technology  
Refinement

In-house niche product  
business

- Unique technology
- Highly customized

- Imaging Sensors
- Laser protection products
- Mixed signal IC

# Role of the Industrial Lab

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Chart 24

- Industrial Lab (Teledyne Scientific's) Business Model
- Overlap is very important

# Teledyne has a long history of relationships with Universities

Larry Coldren

Steve Long

Pochi Yeh

Jim Harris

Elliot Brown

John Bowers

Dan Dapkus

Wen-Wang

David Clark

Peter Asbeck

Herbert Kroemer

Frank Chang

Dave Rutledge

...



CALTECH



STANFORD



SANTA CRUZ



# Role of the Industrial Lab

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Chart 26

- Industrial Lab (Teledyne Scientific's) Business Model
- Overlap is very important
- Truth is stranger than fiction

# Role of the Industrial Lab

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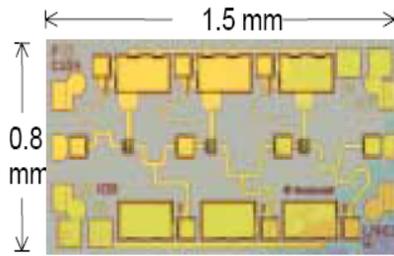
Chart 27

- Industrial Lab (Teledyne Scientific's) Business Model
- Overlap is very important
- Truth is stranger than fiction (profit is not a four-letter word)

# Ka-Band GaAs PHEMT LNA Mil-B LRIP

**Ka-band LNA MMIC  
Mil-Class B Reliability  
(0.18  $\mu$ m GaAs PHEMT)**

24 dB Gain  
2.5 dB NF  
at 35 GHz



- Supplied MMICs from TSC Fab for 10 years
- Qty 500/year at about \$1000/die
- Mil Spec-B
- Last delivery 2003



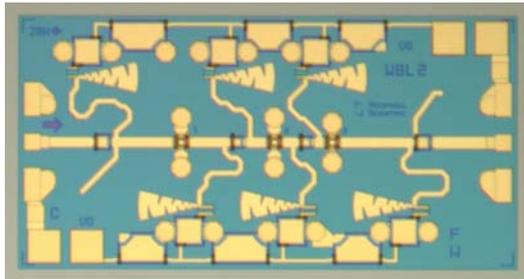
LNA for PAC-3 missile

TRL 9

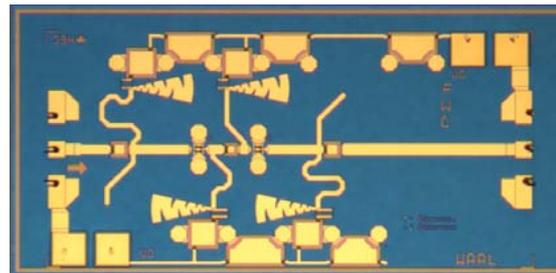


# High Performance Technologies at Teledyne

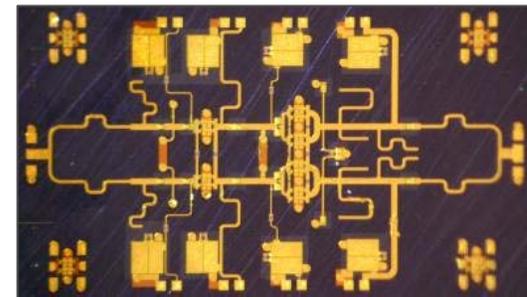
### InP HEMT



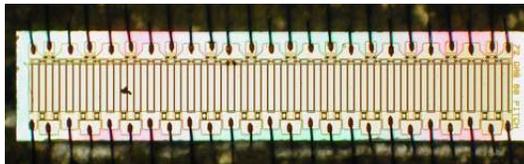
### ABCS HEMT



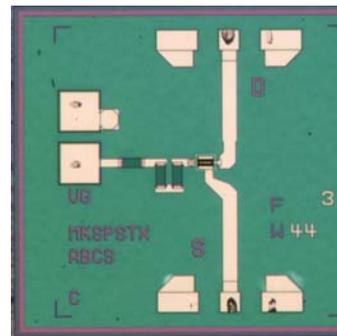
### GaN HEMT



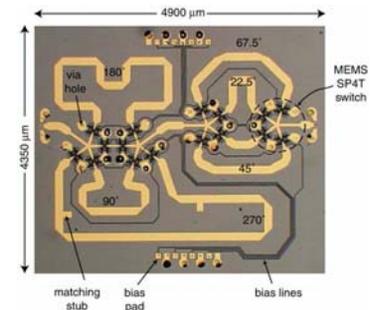
### SiC MESFET



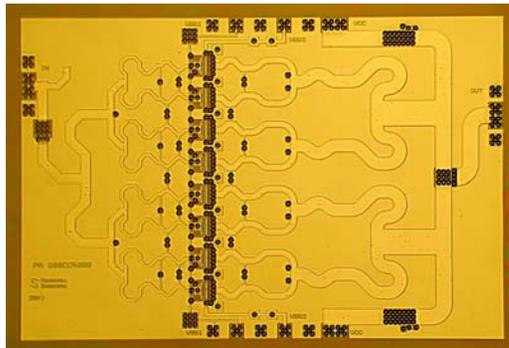
### ABCS HEMT Switches



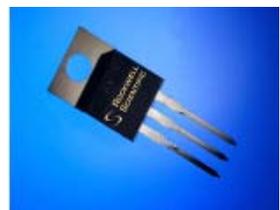
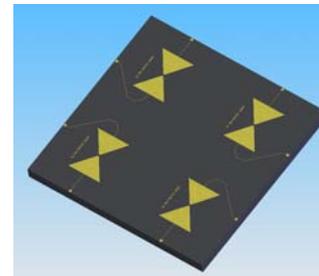
### MEMS Switches



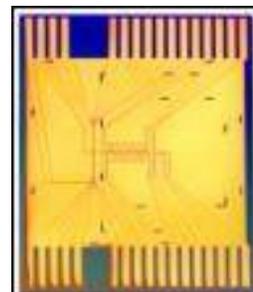
### InP HBT



### mmW Detectors

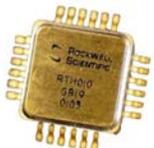


### SiC Schottkys and FETs



### Atom Chips

# Mixed-Signal Integrated Circuits



TH	Fclk (GHz)	Bandwidth (GHz)	Hold Time (ns)	FSR (V)	Supply (V)	Power (W)	Availability	Notes
RTH010	1	9	10	1.0	-5.2/5.0	1.6	Now	Dual Track and Hold
RTH020	1	12	10	1.0	-5.2/5.0	1.6	Now	Dual Track and Hold
RTH030	1	8	60	1.0	-5.2/5.0	1.9	Now	Low Noise
RTH040	1	11	50	1.0	-5.2/5.0	1.6	Now	Longer Hold Time
RTH050	1	15	50	1.0	-5.2/5.0	1.6	Now	Dual Track and Hold
RTH060	4	16	5	2.0	-5.2/5.0	1.5	Now	Dual Track and Hold

DAC	Resolution (Bit)	Fclk (GHz)	Bandwidth (GHz)	SFDR (dB)	Supply (V)	Power (W)	Availability	Notes
RDA012	12	1	0.5	65	-5.2	1.8	Now	ECL inputs
RDA012LP	12	1.5	0.75	60	3.3	0.7	Now	Low Power
RDA012M4	12	1.3	0.65	50	-5.2/3.3	3.4	Now	4:1 MUXDAC
RDA012M4MS	12	1.3	0.65	50	-5.2/3.3	3.4	Now	4:1 Master Slave MUXDAC
RDA012RZ	12	1	1	55	-5.2/3.3	3.6	Now	Return to Zero
RDA112RZ	12	1.5	1.5	50	-5.2/3.3	3.6	Now	Return to Zero



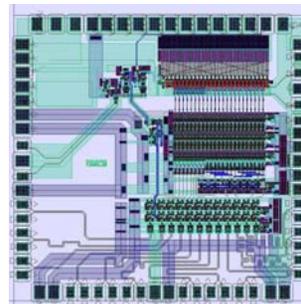
# ADC, DDFS and Logic



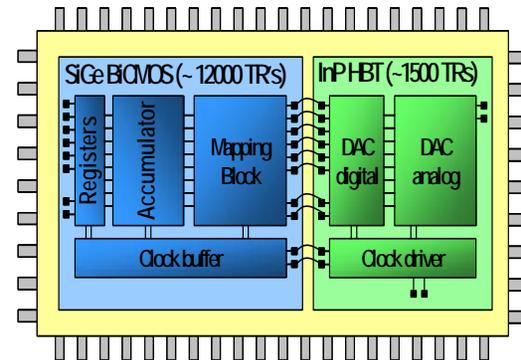
ADC	Resolution (Bit)	Fclk (GHz)	Bandwidth (GHz)	SFDR (dB)	Supply (V)	Power (W)	Availability	Notes
RAD004	6	4	6	30	-5.2/3.3/5.0	6.0	Samples	6Bit 4GS/s Grey Code Output
DDFS	Resolution (Bit)	Fclk (MHz)	Tuning Word (Bits)	I/O Interface	Supply (V)	Power (W)	Availability	Notes
RDS010	12	900	32	Parallel	3.3	2.5	Now	32Bit FCW, 12Bit PCW
LOGIC	Bus Width (Bit)	Fclk (GHz)	Control Interface	I/O	Supply (V)	Power (W)	Availability	Notes
RDX004M4	10	4	Parallel	LVDS	-5.2/3.3	6.0	Samples	1:4 10Bit Demultiplexer



**Present State of the Art**  
60dB SFDR at 1GHz



4GS/s InP DAC



4GS/s Hybrid DDS

# Role of the Industrial Lab

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Chart 32

- Industrial Lab (Teledyne Scientific's) Business Model
- Overlap is very important
- Truth is stranger than fiction (profit is not a four-letter word)
- Industrial users provide specifications

# Role of the Industrial Lab

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Chart 33

- Industrial Lab (Teledyne Scientific's) Business Model
- Overlap is very important
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- Industrial users provide specifications
- Technology transition is paramount

# Role of the Industrial Lab

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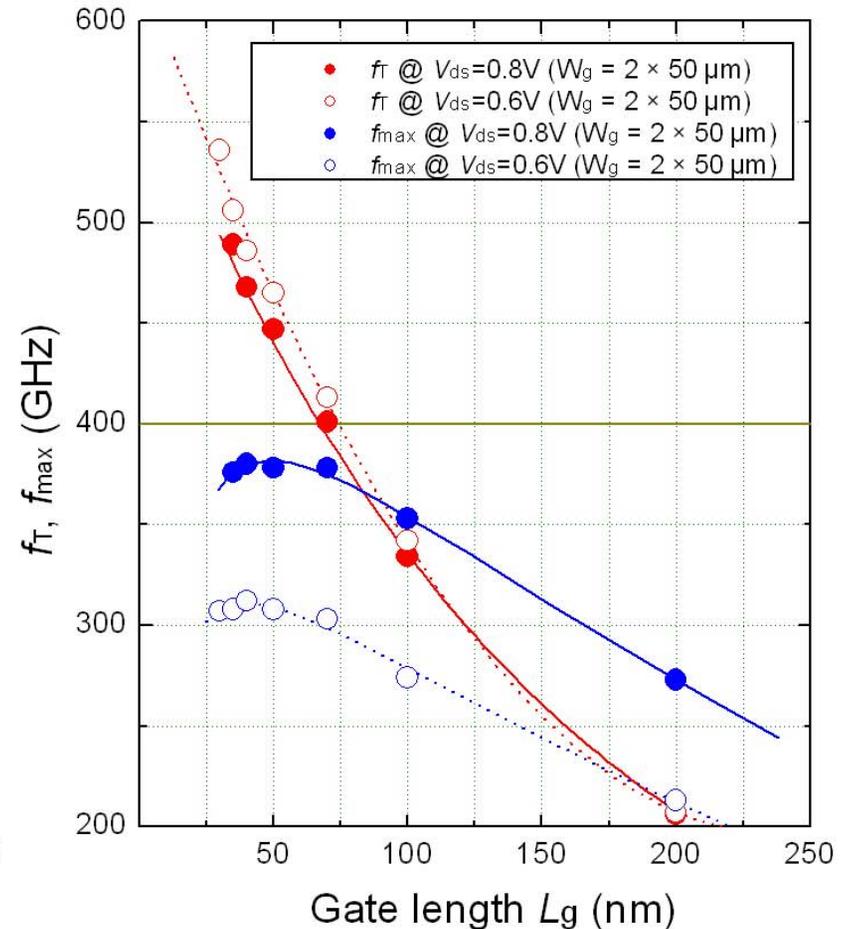
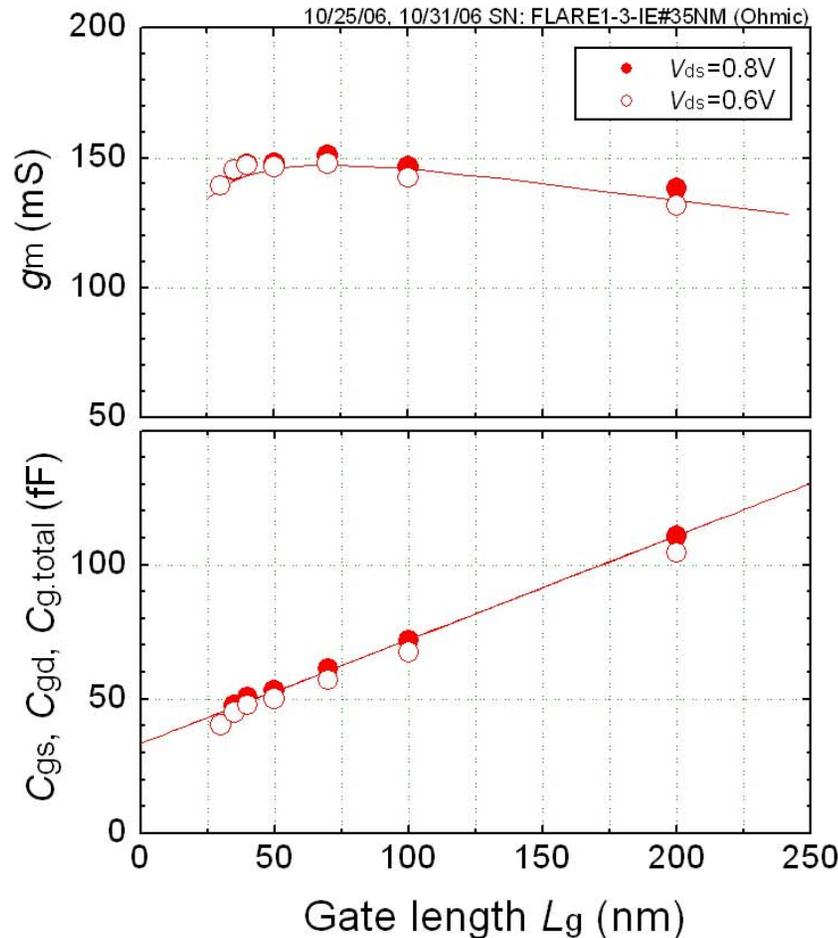
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Chart 34

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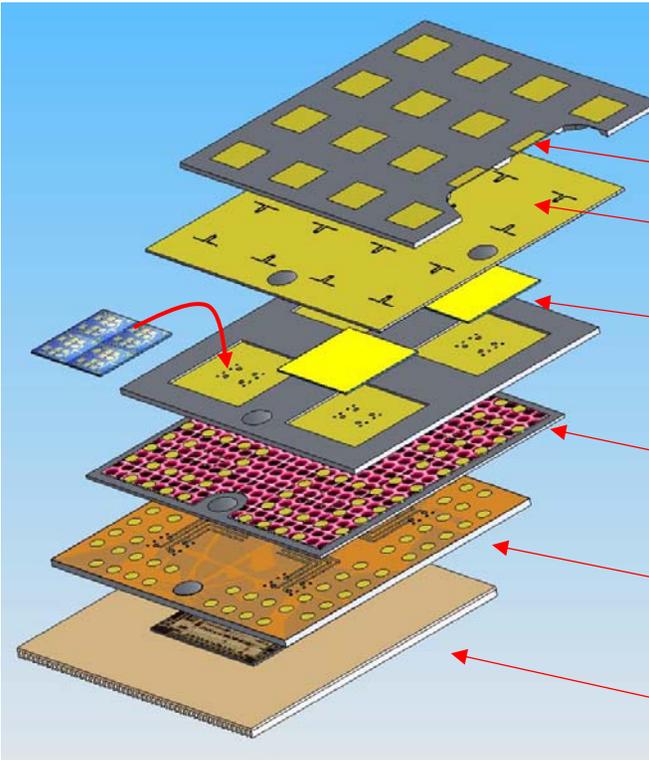
# Precise process control enables understanding of scaling behavior through $L_g$ -dependence

## Gate Length Dependence of RF Parameters for InP-HEMTs



# Scalable Millimeter-wave Architectures for Reconfigurable Transceivers (SMART)

Our goal is to demonstrate a 44-GHz Transceiver Array that integrates all required functionality from Silicon digital beam control and rf beamforming electronics to InP ultra-high power amplifiers and sensitive receivers, with wide-scan apertures, into a compact, rugged, micromachined three-dimensional structure.



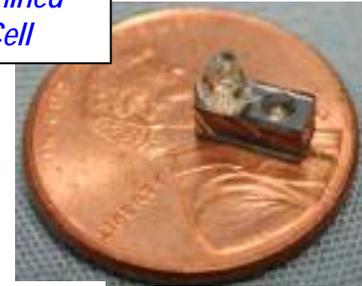
<u>SLIC Stack</u>	<u>Function</u>
<b>Planar antenna layer</b>	Compact multi layer patch antenna provides high isolation from each element with large bandwidth and multiband functionality. Antenna efficiencies of 75% is possible due to multi-stack coupling design.
<b>III-V Chip Interposer</b>	SMMW InP DHBT transistors are used at Q-band to provide the heart of a highly efficient compact power amplifiers with 10W/cm <sup>2</sup> power density. This is achieved by multistack low profile 3D BCB stripline transmission line impedance matching
<b>Heat Spreader</b>	The generated heat throughout SLIC is transferred through strategically located thermal vias to the heat spreader. This is a novel passive two-phase micro-channel array covered with a micro/nano wick structure increasing the effective surface area by > 10x
<b>IC Interconnect layer</b>	The Interposers integrate all the components together. Impressive array of via technologies will be used to deliver RF, bias and control signals to the entire SLIC stack. Low resistance multistack connections will be used to eliminate cross talk and improve efficiency of the SLIC
<b>Silicon beam forming IC</b>	Digital beam forming eliminates long transmission line phase-shifting networks within the beamsteerer, and exploits active transistor circuits for all functions. This is enabled by switching an efficient array of MxM mixers fabricated by Jazz SiGe process.



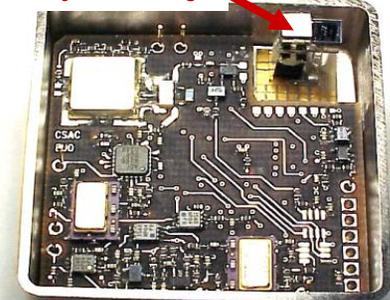
# RSC Chip Scale Atomic Clock Program

- RSC team developing compact, high-performance atomic time/frequency standard for DoD system insertion
- Aggressive program goals:
  - Fractional frequency stability  $<10^{-11}$  (@1hr integration time)
  - Size  $<1\text{cm}^3$
  - Power consumption  $<30\text{mW}$
- Interim prototypes demonstrate excellent performance:
  - **Size  $<10\text{cc}$ , power  $<200\text{mW}$ , Allan Deviation  $<6 \times 10^{-11}$  (100sec)**

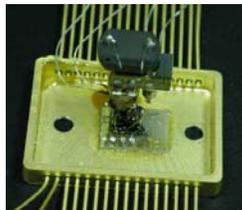
*Micromachined Vapor Cell*



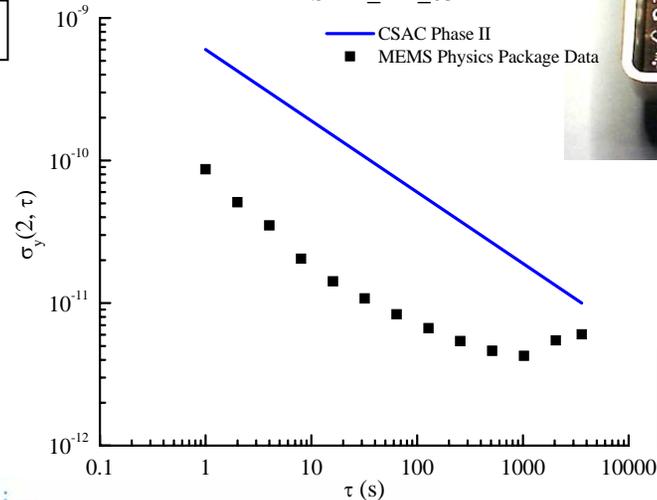
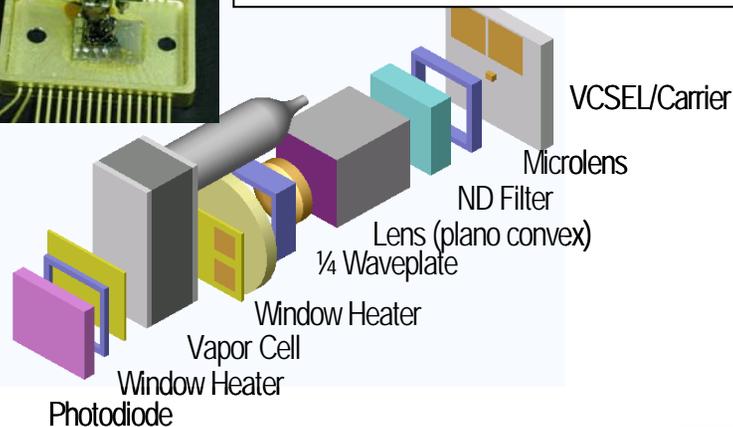
*Physics Package*



*Compact Control Electronics*



*Photo, schematic of CSAC prototype*



*Measured Allan Deviation of CSAC*

# Outline

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- Why Darpa is important
- Role of the University
- Role of the Industrial Lab
- Rules of Engagement

# Rules of Engagement (Univeristy + Industry)

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Chart 39

- Partner with industry (different roles)
- Who is in the critical path?
- Who is the prime contractor?
- Watch out for stovepipes

# Rules of Engagement

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- Partner with industry (different roles)
- Who is in the critical path?
- Who is the prime contractor?
- Watch out for stovepipes
- Think long-term – put it on the shelf

# Rules of Engagement

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- Partner with industry (different roles)
  - Who is in the critical path?
  - Who is the prime contractor?
  - Watch out for stovepipes
  - Think long-term – put it on the shelf
- 
- 
- Keep it simple (distill or drown)

# Rules of Engagement

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- Partner with industry (different roles)
  - Who is in the critical path?
  - Who is the prime contractor?
  - Watch out for stovepipes
  - Think long-term – put it on the shelf
- 
- Keep it simple (distill or drown)
  - No shopping lists

# Rules of Engagement

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- Partner with industry (different roles)
  - Who is in the critical path?
  - Who is the prime contractor?
  - Watch out for stovepipes
  - Think long-term – put it on the shelf
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- Keep it simple (distill or drown)
  - No shopping lists
  - Don't beat a dead horse

# Summary

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Chart 45

## University + Darpa + Industry

# Summary

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University + Darpa + Industry

= A ~perfect partnership

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